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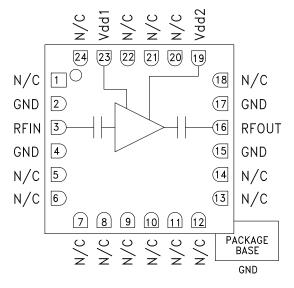


# **Typical Applications**

The HMC564LC4 is ideal for use as a LNA or driver amplifier for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- Test Equipment and Sensors
- Military & Space

#### **Functional Diagram**



# GaAs SMT pHEMT LOW NOISE AMPLIFIER, 7 - 14 GHz

HMC564LC4

#### Features

Noise Figure: 1.8 dB Gain: 17 dB OIP3: 25 dBm Single Supply: +3V @ 51 mA 50 Ohm Matched Input/Output RoHS Compliant 4 x 4 mm Package

#### **General Description**

The HMC564LC4 is a high dynamic range GaAs pHEMT MMIC Low Noise Amplifier housed in a leadless RoHS compliant 4x4 mm SMT package. Operating from 7 to 14 GHz, the HMC564LC4 features extremely flat small signal gain of 17 dB as well as 1.8 dB noise figure and +25 dBm output IP3 across the operating band. This self-biased LNA is ideal for microwave radios due to its consistent output power, single +3V supply operation, and DC blocked RF I/O's.

#### Electrical Specifications, $T_{A} = +25^{\circ}$ C, Vdd 1, 2 = +3V

Parameter	Min.	Тур.	Max.	Units
Frequency Range		7 - 14		GHz
Gain	14	17		dB
Gain Variation Over Temperature		0.02	0.03	dB/ °C
Noise Figure		1.8	2.2	dB
Input Return Loss		15		dB
Output Return Loss		14		dB
Output Power for 1 dB Compression (P1dB)	10	13		dBm
Saturated Output Power (Psat)		14.5		dBm
Output Third Order Intercept (IP3)		25		dBm
Supply Current (Idd)(Vdd = +3V)		51	75	mA

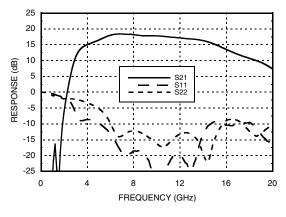
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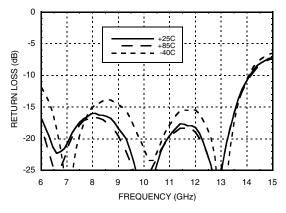
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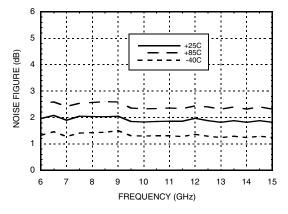
#### **Broadband Gain & Return Loss**



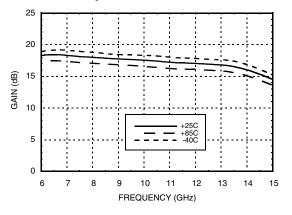
Input Return Loss vs. Temperature



Noise Figure vs. Temperature



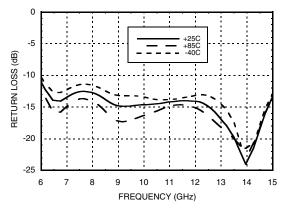
#### Gain vs. Temperature



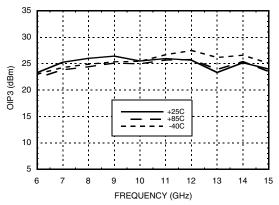
GaAs SMT pHEMT LOW NOISE

AMPLIFIER, 7 - 14 GHz

#### Output Return Loss vs. Temperature



## Output IP3 vs. Temperature



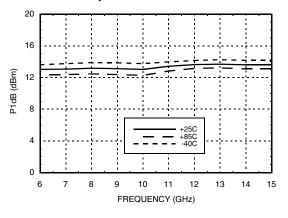
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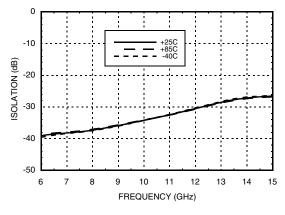
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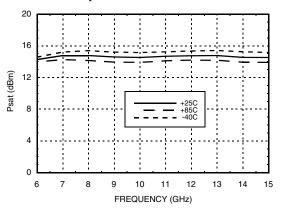
#### P1dB vs. Temperature



**Reverse Isolation vs. Temperature** 



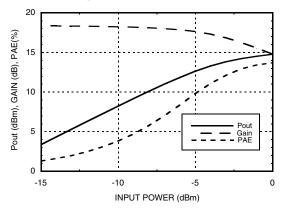
#### Psat vs. Temperature



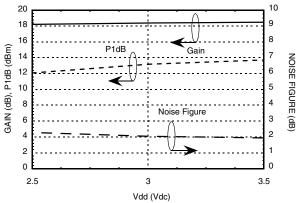
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#### Power Compression @ 8 GHz







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## Absolute Maximum Ratings

Drain Bias Voltage (Vdd1, Vdd2)	+3.5 Vdc
RF Input Power (RFIN) (Vdd = +3.0 Vdc)	+5 dBm
Channel Temperature	175 °C
Continuous Pdiss (T= 85 °C) (derate 12.9 mW/°C above 85 °C)	1.16 W
Thermal Resistance (channel to ground paddle)	77.5 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A

# GaAs SMT pHEMT LOW NOISE AMPLIFIER, 7 - 14 GHz

# Typical Supply Current vs. Vdd

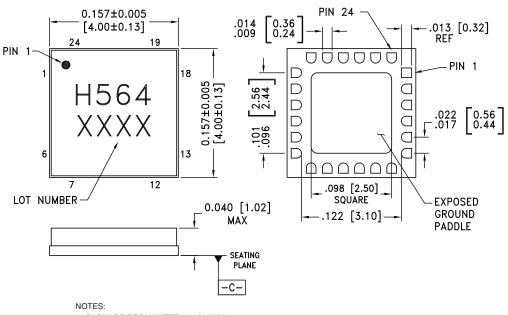
Vdd (V)	ldd (mA)
2.5	49
3.0	51
3.5	53

Note: Amplifier will operate over full voltage ranges shown above.



## **Outline Drawing**

#### BOTTOM VIEW



- 1. PACKAGE BODY MATERIAL: ALUMINA.
- 2. LEAD AND GROUND PADDLE PLATING: GOLD FLASH OVER NICKEL.
- 3. DIMENSIONS ARE IN INCHES (MILLIMETERS).
- 4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05MM DATUM
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

#### **Package Information**

[	Part Number	Package Body Material Lead Finish MSL Ratio		MSL Rating	Package Marking [2]	
	HMC564LC4	Alumina, White	Gold over Nickel	MSL3 <sup>[1]</sup>	H564 XXXX	

[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX

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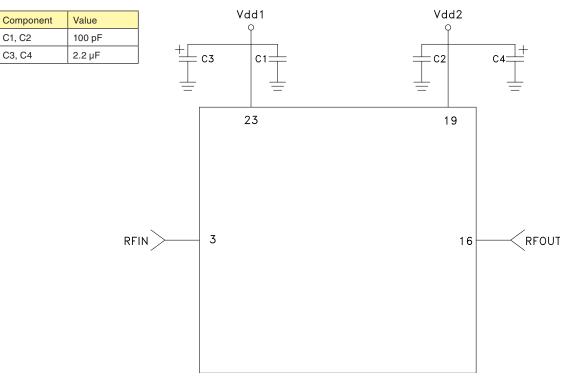
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# GaAs SMT pHEMT LOW NOISE AMPLIFIER, 7 - 14 GHz

## **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1, 5 -14, 18, 20, 21, 22, 24	N/C	No connection required. These pins may be connected to RF/ DC ground without affecting performance.	
2, 4, 15, 17	GND	These pins and package bottom must be connected to RF/DC ground.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	
16	RFOUT	This pin is AC coupled and matched to 50 Ohms.	○ RFOUT
19, 23	Vdd1, Vdd2	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF, and 2.2 μF are required.	•Vdd1,2 

# **Application Circuit**



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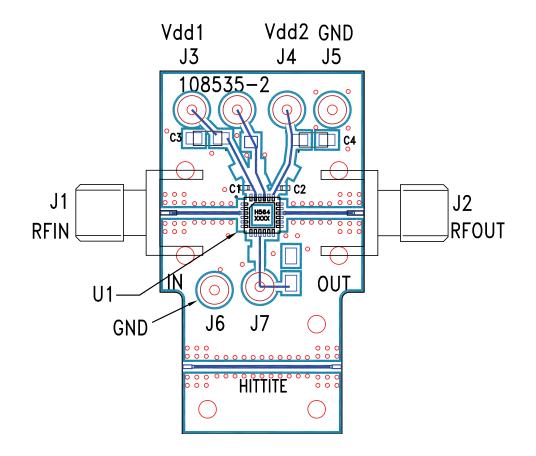


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## **Evaluation PCB**



## List of Material for Evaluation PCB 116156 [1]

Item	Description
J1, J2	2.92 mm PC mount SMA
J3 - J7	DC Pin
C1 - C2	100 pF capacitor, 0402 Pkg
C3 - C4	2.2µF Capacitor, Tantalum
U1	HMC564LC4 Amplifier
PCB [2]	108535 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350.

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

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